## 2SD1323

## Silicon NPN triple diffusion planar type Darlington

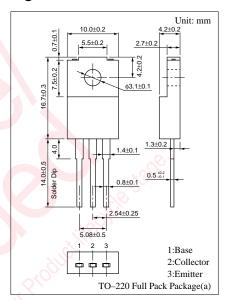
## For midium speed power switching

### Features

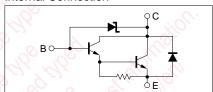
- Incorporating a zener diode of 30V zener voltage between collector and base
- Minimized variation in the breakdown voltage
- Large energy handling capability
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

## Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	V <sub>CBO</sub>	30±5	V	
Collector to emitter voltage	$V_{CEO}$	30±5	V	
Emitter to base voltage	$V_{EBO}$	5	V	
Peak collector current	I <sub>CP</sub>	8	A	
Collector current	$I_{C}$	4	A	
Collector power T <sub>C</sub> =25°C	D	40	***	
dissipation Ta=25°C	$P_{\rm C}$	2	W	
Junction temperature	$T_{\rm j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	CC V	



#### Internal Connection



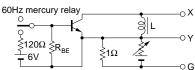
#### Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 25V, I_E = 0$	30	%)	100	μΑ
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$		Ö	2	mA
Collector to emitter voltage	$V_{CEO}$	$I_C = 5 \text{mA}, I_B = 0$	25		35	V
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 3V, I_{C} = 0.5A$	1000			
	h <sub>FE2</sub> *1	$V_{CE} = 3V$ , $I_C = 3A$	2000		10000	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3A, I_B = 12mA$			2.5	V
		$I_C = 5A, I_B = 20mA$			4	
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 3A, I_B = 12mA$			2.5	V
Transition frequency	$f_{T}$	$V_{CE} = 10V, I_{C} = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = 3A$ , $I_{B1} = 12mA$ , $I_{B2} = -12mA$ ,		0.3		μs
Storage time	t <sub>stg</sub>			3		μs
Fall time	$t_{\rm f}$	$V_{CC} = 20V$		1		μs
Energy handling capability	$E_{s/b}^{*2}$	$I_C = 2A, L = 100mH, R_{BE} = 100\Omega$	200			mJ

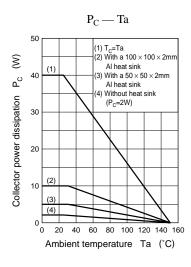
#### \*1h<sub>FE2</sub> Rank classification

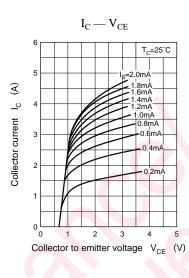
Rank	Q	P
$h_{FE2}$	2000 to 5000	4000 to 10000

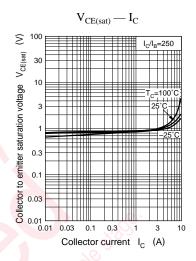


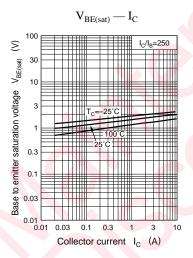


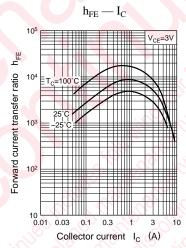
Power Transistors 2SD1323

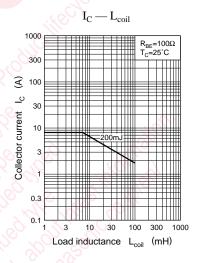




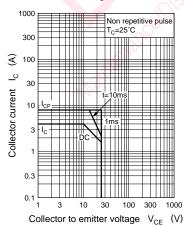








Area of safe operation (ASO)



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